

# High gain amplifier transistor (25V, 2A)

#### 2SD2153

#### ●Features

- 1) Low saturation voltage, typically  $V_{CE(sat)} = 0.12V$  at  $I_C = I_B = 1A/20mA$
- 2) Excellent DC current gain characteristics.

## ●Dimensions (Unit: mm) (1) Base (2) Collector (3) Emitter ROHM: MPT3 EIAJ : SC-62 SOT-89

#### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	30	V	
Collector-emitter voltage	Vceo	25	V	
Emitter-base voltage	VEBO	6	V	
Collector current	Ic	2	A(DC)	
	IC IC	3	A(Pulse) *1	
Collector power dissipation	Pc	0.5	· W	
	PC PC	2 *2		
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

#### ●Packaging specifications and hfe

Туре	2SD2153
Package	MPT3
hfe	UVW
Marking	DN *
Code	T100
Basic ordering unit (pieces)	1000

#### ●Electrical characteristics (Ta=25°C)

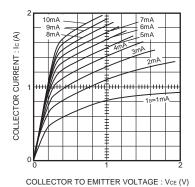
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	30	-	-	V	Ic=50μA	
Collector-emitter breakdown voltage	BVceo	25	-	-	V	Ic=1mA	
Emitter-base breakdown voltage	ВУЕВО	6	-	-	V	Iε=50μA	
Collector cutoff current	Ісво	-	-	0.5	μА	Vcb=20V	
Emitter cutoff current	Ієво	-	-	0.5	μΑ	V <sub>EB</sub> =5V	
Collector-emitter saturation voltage	VCE(sat)	-	0.12	0.5	V	Ic/I <sub>B</sub> =1A/20mA	*
DC current transfer ratio	hfe	820	-	1800	-	Vce/Ic=6V/0.5A	
Transition frequency	f⊤	-	110	-	MHz	Vc=10V, I=-10mA, f= 100MHz	
Output capacitance	Cob	-	22	-	pF	Vcb=10V, IE=0A, f=1MHz	

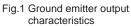
<sup>\*</sup> Measured using pulse current.

<sup>\*1</sup> Single pulse, Pw=10ms \*2 Mounted on a 40×40×¹0.7mm Ceramic substrate

2SD2153 **Data Sheet** 

#### •Electrical characteristics curves





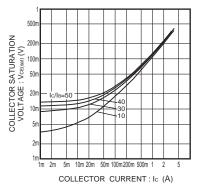


Fig.4 Collector-emitter saturation voltage vs. collector current

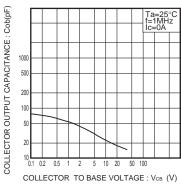


Fig.7 Collector output capacitance vs. collector-base voltage

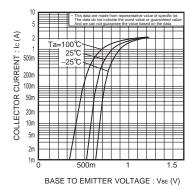


Fig.2 Ground emitter propagation characteristics

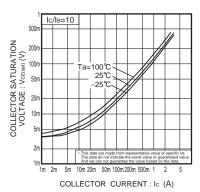


Fig.5 Collector-emitter saturation voltage vs. collector current

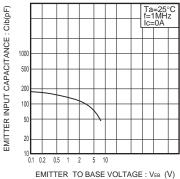


Fig.8 Emitter input capacitance vs. emitter-base voltage

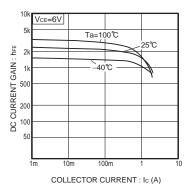


Fig.3 DC current gain

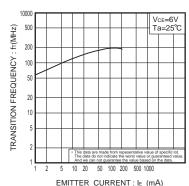


Fig.6 Gain bandwith product vs. emitter current

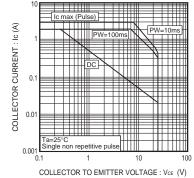


Fig.9 Safe operating area

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